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February 7, 2001

TO: Commissioner for Patents  
Attn: George C. Eckert II  
Patent Examining Corps  
Facsimile Center  
Washington, D.C. 20231

FROM: Robert E. MatesOUR REF: 303.356US1TELEPHONE: (612) 373-6973FAX NUMBER (703) 305-3431

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\* Please deliver to Examiner George C. Eckert II in Art Unit 2815. \*

Document(s) Transmitted: Amendment and Response Under 37 CFR 1.116 (20 pgs)Total pages of this transmission, including cover letter: 21 pgs

If you do NOT receive all of the pages described above, please telephone us at 612-373-6900, or fax us at 612-339-3061.

In re. Patent Application of: Leonard Forbes et al.Examiner: George C. Eckert IISerial No.: 08/902,133Group Art Unit: 2815Filed: July 29, 1997Docket No.: 303.356US1Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY  
MEMORY DEVICE

Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

By: [Signature]Name: Robert E. MatesReg. No.: Reg. No. 35,271

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## EXPEDITED PROCEDURE - EXAMINING GROUP 2815

S/N 08/902,133PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: George C. Eckert II

Serial No.: 08/902,133

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.356US1

Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ  
ONLY MEMORY DEVICEAMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116Box AF  
Commissioner for Patents  
Washington, D.C. 20231

In response to the final Office Action dated 20 September 2000, please amend the application as follows:

IN THE CLAIMS

Please cancel claims 1, 7, 11, 16, 33, and 38.

Please amend the claims as follows:

2. [Amended] The memory cell of claim [1] 2, wherein materials comprising at least one of the storage electrode and the insulator are selected to have an electron affinity causing the barrier energy to be selected at less than approximately 3.3 eV.

6. [Amended] The memory cell of claim [1] 2, wherein the insulator comprises a material that has a material composition that is selected to obtain a larger electron affinity than silicon dioxide.

7. [Amended] The memory cell of claim [1] 2, wherein the barrier energy is less than approximately 2.0 eV.

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